In the claims:

Following is a complete set of claims as amended with this Response.

1. (Currently Amended) A method comprising:

initiating a flow of set up gases into a plasma enhanced sequential chemical vapor deposition (PECVD) chamber;

establishing an operational pressure in the chamber;

keeping a deposition gas out of the chamber;

applying plasma power in a radio frequency (RF) form to the chamber;

introducing a flow of the deposition gas into the chamber after applying the plasma power during the application of plasma power;

starting nitride deposition in the chamber from the deposition gas to form a first portion of a layer on a substrate based on the application of plasma power;

stopping the flow of the deposition gas into the chamber during the application of plasma power; ~~and~~

turning off the plasma power after the flow of deposition gas is stopped;

reapplying plasma power;

reintroducing a deposition gas after reapplying the plasma power;

starting nitride deposition in the chamber to form a second portion of the layer on the substrate after reapplying the plasma power; and

turning off the plasma power.

2. (Canceled)

3. (Currently Amended) The method of Claim 1 ~~Claim 2~~, wherein introducing a deposition gas comprises introducing silane gas.

4. (Currently Amended) The method of Claim 1 ~~Claim 2~~, wherein introducing silane gas comprises introducing silane gas at least 0.5 seconds after applying plasma power.

5. (Currently Amended) The method of Claim 1 ~~Claim 2~~, wherein introducing silane gas comprises diverting silane gas from a pump to the deposition chamber.

6. (Canceled)

7. (Previously Presented) The method of Claim 1, wherein initiating set-up gas flow comprises flowing ammonia and nitrogen gases into the chamber.

8. (Currently Amended) The method of Claim 1 ~~Claim 2~~, further comprising pumping away residue gases after turning off the plasma power and before reapplying the plasma power.

9. (Canceled).

10. (Currently Amended)The method of Claim 1 ~~Claim 2~~, further comprising moving the wafer to another chemical vapor deposition position after forming the first portion of the layer and before forming the second portion of the layer.

11. (Original)The method of Claim 1, further comprising repeating turning on and off the nitride supply and the plasma power substantially simultaneously until a complete layer is formed.

12-20. (Canceled)

21. (Withdrawn) An apparatus having a first portion of a nitride deposition layer formed on a substrate in a plasma enhanced sequential chemical vapor deposition chamber in accordance with the method of Claim 1.

22. (Withdrawn) The apparatus of Claim 21, wherein the layer is a nitride etch stop layer.

23. (Withdrawn) The apparatus of Claim 21, wherein, the layer has no intra-film interfaces corresponding to transitions of the sequential chemical vapor deposition formation.

24. (Withdrawn) The apparatus of Claim 14 wherein the layer is a nitride etch stop layer.

25. (Withdrawn) The apparatus of Claim 14 wherein the layer is a silicon nitride layer.

26. (Withdrawn) The apparatus of Claim 14 wherein the layer is an insulating layer for a gate of a flash memory transistor.

27. (Withdrawn) The apparatus of Claim 21, further comprising:

a drain area;

a source area; and

a gate layer coupled to the drain area and the source area;

wherein the layer overlies the gate layer, the nitride layer having no intra-film interfaces corresponding to transitions of the sequential deposition.